

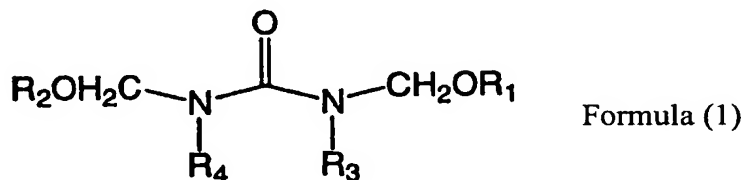
**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-3. (Canceled)
4. (Previously Presented) The process for manufacturing a semiconductor device according to claim 11, wherein the anti-reflective coating forming composition further comprises a light absorbing compound and/or a light absorbing resin.
5. (Previously Presented) The process for manufacturing a semiconductor device according to claim 4, wherein the light-absorbing compound is at least one compound selected from naphthalene compounds and anthracene compounds.
6. (Previously Presented) The process for manufacturing a semiconductor device according to claim 4, wherein the light absorbing compound is at least one compound selected from triazine compounds and triazine trione compounds.
7. (Previously Presented) The process for manufacturing a semiconductor device according to claim 4, wherein the light absorbing resin is a resin having in the structure at least one aromatic ring structure selected from benzene ring, naphthalene ring and anthracene ring.
8. (Previously Presented) The process for manufacturing a semiconductor device according to claim 11, wherein the anti-reflective coating forming composition further comprises a resin having at least one crosslink-forming substituent selected from hydroxy group, carboxy group, amino group and thiol group.
- 9-10. (Canceled)
11. (Currently Amended) A process for manufacturing a semiconductor device, characterized by comprising the steps of:  
  
coating an anti-reflective coating forming composition on a substrate and

baking it to form an anti-reflective coating;

wherein the anti-reflective coating forming composition comprises a resin produced by a condensation reaction between compounds of formula (1),



wherein R<sub>1</sub> and R<sub>2</sub> are independently of each other hydrogen atom or an alkyl group, R<sub>3</sub> and R<sub>4</sub> are independently of each other hydrogen atom, methyl group, ethyl group, hydroxymethyl group or an alkoxymethyl group, and an acid and/or acid generator,

the resin produced from the condensation reaction between compounds of formula (1) has a weight average molecular weight of 200 to 500,000, and

the resin produced from compounds of formula (1) is contained in an amount of more than 50 mass% ~~or more~~ in a solid content of the anti-reflective coating forming composition;

forming a photoresist on top of the anti-reflective coating;

exposing the substrate covered with the anti-reflective coating and the photoresist with a light;

developing it;

transferring an image on the substrate by etching to form an integrated circuit device.

12. (Previously Presented) The process for manufacturing a semiconductor device according to claim 11, wherein the resin produced from the condensation reaction between compounds of formula (1) have urea moieties linked through -CH<sub>2</sub>- or -CH<sub>2</sub>OCH<sub>2</sub>-.

13. (Currently Amended) The process for manufacturing a semiconductor device according to claim 11, wherein the resin produced from the condensation reaction between compounds of formula (1) ~~are~~is in an amount of 60 to 95 mass% in a solid content of the anti-reflective coating forming composition.

14. (Canceled)